Part Number	Customer

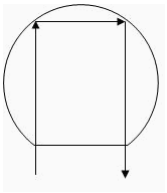
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	None	
	5.0	Secondary Flat Length	0.00 +/- 0.00 mm	Wafer Vendor
	6.0	Overall Thickness	353.00 +/- 13.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	8.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	9.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	Guaranteed by process
	12.0	Edge Rounding	Yes	Wafer Vendor
	13.0	Lasermarking	On wafer BACKSIDE for identification. Scribe format: YYMM-XXXXX (unique scribe)	
HandleSilicon	14.0	Handle Growth Method	CZ	Wafer Vendor
	15.0	Handle Orientation	{100} +/-1.0 degree	Wafer Vendor
	16.0	Handle Thickness	300.00 +/- 10.00 µm	ADE, 100%
	17.0	Handle Doping Type	N	Wafer Vendor
	18.0	Handle Dopant	Phosphorous	Wafer Vendor
	19.0	Handle Resistivity	1 - 5 Ohmcm	Wafer Vendor
	20.0	Backside Finish	Device layer #2	Guaranteed by Process
BuriedOxide	21.0	Oxide Type	Thermal	
	22.0	Oxide Thickness	5,000.00 +/- 250.00 A	Nanospec centre point, 4%
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	25.0	Nominal Thickness	26.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorous	Wafer Vendor
	28.0	Device Resistivity	1 - 5 Ohmcm	Wafer Vendor
	29.0	Oxygen Concentration	6 - 18 ppma	Wafer Vendor
BuriedOxide2	30.0	Oxide 2 Type	Thermal	
	31.0	Oxide 2 Thickness	5,000.00 +/- 250.00 A	Nanospec centre point measurement, 4%
DeviceSilicon2	32.0	Device 2 Growth Method	CZ	Wafer Vendor
	33.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	34.0	Device 2 Nominal Thickness	26.00 +/- 1.00 um	FTIR, 100% 9-point measurement (see note 3)

Part Number	Customer

Category		Parameter	Specification	Measurement Method
DeviceSilicon2	35.0	Device 2 DopingType	N	Wafer Vendor
	36.0	Device 2 Dopant	Phosphorous	Wafer Vendor
	37.0	Device 2 Resistivity	1 - 5 Ohmcm	Wafer Vendor
	38.0	Oxygen Concentration 2	6 - 18 ppma	Wafer Vendor
DeviceSilicon	39.0	Voids	none	Bright Light, 100% (note 2)
	40.0	Scratches	0	Bright Light, 100% (note 2)
	41.0	Haze	none	Bright Light, 100% (note 2)

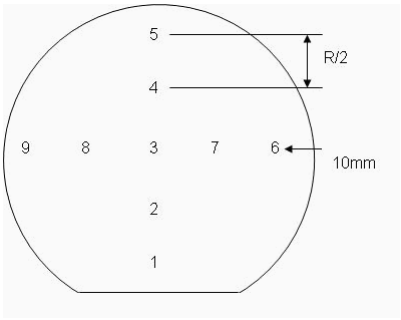
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information